L Number	Hits		DB	Time stamp
-	770	(250/330 or 250/332 or 250/338.1 or	USPAT;	2003/05/31 17:14
		250/338.3 or 250/338.4) and (ir or	US-PGPUB;	-
		infrared) and resistor	EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	128		USPAT;	2003/06/02 19:18
		250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	
		250/340) and (ir or infrared) and resistor	EPO; JPO;	1
		and shield	DERWENT;	1
			IBM_TDB	
	163	(250/330 or 250/332 or 250/338.1 or	USPAT;	2003/06/02 19:18
		250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	
		250/340) and (ir or infrared) and resistor	EPO; JPO;	
		and (shield or shielding)	DERWENT;	
			IBM_TDB	
	1	(250/330 or 250/332 or 250/338.1 or	USPAT;	2003/06/02 14:34
		250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	
		250/340) and (ir or infrared) and resistor	EPO; JPO;	
		and (shield or shielding) and overhang	DERWENT;	
			IBM_TDB	1
-	6		USPAT;	2003/06/02 14:38
		250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	1
		250/340) and (ir or infrared) and resistor	EPO; JPO;	
		and (shield or shielding) and hang	DERWENT;	
		M	IBM_TDB	1
	37	(250/330 or 250/332 or 250/338.1 or	USPAT;	2003/06/02 19:18
		250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	
		250/340) and (ir or infrared) and resistor	EPO; JPO;	1
		and (shield or shielding) and pixel	DERWENT;	
		10501000 0501000 0501000 1	IBM_TDB	
-	78	(250/330 or 250/332 or 250/338.1 or	USPAT;	2003/06/02 17:12
į		250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	
		250/340) and (ir or infrared) and resistor	EPO; JPO;	1
		and (shield or shielding) and (reflect or	DERWENT;	
	F 2	reflecting or reflection)	IBM_TDB	0000100100 10 10
-	51	(250/330 or 250/332 or 250/338.1 or 250/338.3 or 250/338.4 or 250/339.2 or	USPAT;	2003/06/02 18:12
		250/338.3 or 250/338.4 or 250/339.2 or 250/340) and (ir or infrared) and resistor	US-PGPUB;	1
			EPO; JPO;	
		and (absorbing) and (silicon adj nitride)	DERWENT; IBM TDB	
	30	(250/330 or 250/332 or 250/338.1 or	USPAT:	2003/06/02 18:14
-	30	250/338.3 or 250/338.4 or 250/339.2 or		2003/06/02 18:14
		250/338.3 or 250/338.4 or 250/339.2 or 250/340) and (ir or infrared) and resistor	US-PGPUB; EPO; JPO;	
i		and (absorbing) and (silicon adj oxide)	DERWENT;	
-	20	(250/330 or 250/332 or 250/338.1 or	IBM TDB USPAT;	2003/06/02 18:16
	36	250/338.3 or 250/338.4 or 250/339.2 or	US-PGPUB;	2003/00/02 18:16
		250/338.3 Or 250/338.4 Or 250/339.2 Or   250/340) and (ir or infrared) and resistor		
			EPO; JPO;	
		and (absorbing adj layer)	DERWENT;	
-	05.6	(050 (330 - 050 (330 - 050 (330 1	IBM_TDB	0000 (00 (00 00 00
	256	(250/330 or 250/332 or 250/338.1 or 250/338.3 or 250/338.4 or 250/339.2 or	USPAT;	2003/06/02 18:34
			US-PGPUB;	
		250/340) and (ir or infrared) and resistor	EPO; JPO;	
1		and (absorbing or absorb)	DERWENT;	
			IBM TDB	1